## DECLARATION FOR NON-PROVISIONAL PATENT APPLICATION

As a below named inventor, I hereby declare that:

My residence, post office address and citizenship are as stated below at 201 et seq. beneath my name.

I believe I am the original, first and sole inventor if only one name is listed at 201 below, or an original, first and joint inventor if plural names are listed at 201 et seq. below, of the subject matter which is claimed and for which a patent is sought on the invention entitled

## SEMICONDUCTOR STRUCTURE FOR PROVIDING STRAINED CRYSTALLINE LAYER ON INSULATOR AND METHOD FOR FABRICATING SAME

and for which a patent application:  ightharpoonup is attached hereto and includes amendment(s) filed on		(if applicable)	
☐ was filed in the United States on			
not accompanying application) with amendment(s) filed on _		(if applicable)	
☐ was filed as PCT international Application No	on	and was amended	
under PCT Article 19 on	(if applicable)		
any amendment referred to above.  I acknowledge the duty to disclose information known to me to Regulations, § 1.56.	be material to patentability as defin	ned in Title 37, Code of Federal	
I hereby claim foreign priority benefits under Title 35, United S inventor's certificate listed below and have also identified below	tates Code, § 119(a)-(d) of any for	eign application(s) for patent or	

EARLIEST FOREIGN APPLI	CATION(S), IF ANY, FILI	ED PRIOR TO THE FILING DA	TE OF THE AP	PLICATION	
APPLICATION NUMBER	COUNTRY	DATE OF FILING (day, month, year)	PRIORIT	PRIORITY CLAIMED	
EP 03290230.6	Europe	29/01/2003	▼ YES	□ NO	
EP 03290231.4	Europe	29/01/2003	▼ YES	□ NO	

I hereby claim the benefit under Title 35, United States Code, § 119(e) of any United States provisional application(s) listed below.

PROVISIONAL APPLICATION NUMBER	FILING DATE
60/485,997	July 9, 2003
60/485,998	July 9, 2003

I hereby claim the benefit under Title 35, United States Code. § 120 of any United States application(s) listed below and, insofar as the subject matter of each of the claims of this application is not disclosed in the prior United States application in the manner provided by the first paragraph of Title 35, United States Code § 112, I acknowledge the duty to disclose information known to me which is material to patentability as defined in Title 37, Code of Federal Regulations, § 1.56 which became available between the filing date of the prior application and the national or PCT international filing date of this application:

FILING DATE	STATUS		
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-	FILING DATE	PATENTED PATENTED	PATENTED PENDING

<sup>\*</sup> for use only when the application is assigned to a company, partnership or other organization.

NY:835743.1

I hereby declare that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under Section 1001 of Title 18 of the United States Code and that such willful false statements may jeopardize the validity of the application or any patent issuing thereon.

14.50	<del>,                                     </del>	pardize the validity of the application			
•	FULL NAME OF	LAST NAME	FIRST NAME	MIDDLE NAME	
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		SIGNATURE OF INVENTOR 204		DATE	

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of: Cécile AULNETTE et al.

Application No.:

Group Art Unit:

Filing Date:

Examiner:

For: SEMICONDUCTOR STRUCTURE FOR PROVIDING STRAINED CRYSTALLINE LAYER ON INSULATOR AND METHOD FOR FABRICATING SAME

Attorney Docket No.: 4717-7300

## POWER OF ATTORNEY BY ASSIGNEE AND EXCLUSION OF INVENTOR(S) UNDER 37 C.F.R. 3.71

Commissioner for Patents P.O. Box 1450 Alexandria, Virginia 22313-1450

Sir:

The undersigned assignee of the entire interest in the above-identified subject application hereby appoints Allan A. Fanucci (Reg. No. 30,256) and Daniel J. Hulseberg (Reg. No. 36,554) of WINSTON & STRAWN LLP (Customer No. 28765) to prosecute this application and to transact all business in the United States Patent and Trademark Office connected therewith.

Please direct all correspondence for this application to Customer No. 28765 to the attention of Allan A. Fanucci (telephone 212-294-3311, facsimile 212-294-4700).

An assignment of the entire interest in the above-identified subject application is submitted herewith for recording and a copy is attached. The undersigned has reviewed this assignment and, to the best of his knowledge, title is in the assignee seeking to take action in this application and that he is empowered to act on its behalf.

ASSIGNEE:	S.O.I. TEC SILICON ON INSULATOR TECHNOLOGIES S.A.
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